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Virtex-7 T and XT FPGAs Data Sheet: DC and AC Switching Characteristics

DS183 (v1.14) April 17, 2013 **Preliminary Product Specification**

Introduction

Virtex®-7 T and XT FPGAs are available in -3, -2, -1, and -2L speed grades, with -3 having the highest performance. The -2L devices operate at V_{CCINT} = 1.0V and are screened for lower maximum static power. The speed specification of a -2L device is the same as the -2 speed grade. The -2G speed grade is available in devices utilizing Stacked Silicon Interconnect (SSI) technology. The -2G speed grade supports 12.5 Gb/s GTX or 13.1 Gb/s GTH transceivers as well as the standard -2 speed grade specifications.

Virtex-7 T and XT FPGA DC and AC characteristics are specified in commercial, extended, and industrial temperature ranges. Except for the operating temperature range or unless otherwise noted, all the DC and AC electrical parameters are the same for a particular speed grade (that is, the timing characteristics of a -1 speed grade industrial device are the same as for a -1 speed grade commercial device). However, only selected speed grades and/or devices are available in each temperature range.

All supply voltage and junction temperature specifications are representative of worst-case conditions. The parameters included are common to popular designs and typical applications.

This Virtex-7 T and XT FPGA data sheet, part of an overall set of documentation on the 7 series FPGAs, is available on the Xilinx website at www.xilinx.com/7.

All specifications are subject to change without notice.

DC Characteristics

Table 1: **Absolute Maximum Ratings(1)**

Symbol	Description	Min	Max	Units
FPGA Logic				
V_{CCINT}	Internal supply voltage	–0.5	1.1	V
V_{CCAUX}	Auxiliary supply voltage	–0.5	2.0	V
V_{CCBRAM}	Supply voltage for the block RAM memories	–0.5	1.1	V
V_{CCO}	Output drivers supply voltage for 3.3V HR I/O banks	–0.5	3.6	V
	Output drivers supply voltage for 1.8V HP I/O banks	–0.5	2.0	V
V_{CCAUX_IO}	Auxiliary supply voltage	–0.5	2.06	V
V_{REF}	Input reference voltage	–0.5	2.0	V
V_{IN}(2)(3)(4)	I/O input voltage for 3.3V HR I/O banks	–0.40	V_{CCO} + 0.55	V
	I/O input voltage for 1.8V HP I/O banks	–0.55	V_{CCO} + 0.55	V
	I/O input voltage (when V_{CCO} = 3.3V) for V_{REF} and differential I/O standards except TMDS_33(5)	–0.40	2.625	V
V_{CCBATT}	Key memory battery backup supply	–0.5	2.0	V
GTX and GTH Transceivers				
$V_{MGTAVCC}$	Analog supply voltage for the GTX/GTH transmitter and receiver circuits	–0.5	1.1	V
$V_{MGTAVTT}$	Analog supply voltage for the GTX/GTH transmitter and receiver termination circuits	–0.5	1.32	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for the GTX/GTH transceivers	–0.5	1.935	V
$V_{MGTREFCLK}$	GTX/GTH transceiver reference clock absolute input voltage	–0.5	1.32	V

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
$V_{MGTAVTTRCAL}$	Analog supply voltage for the resistor calibration circuit of the GTX/GTH transceiver column	–0.5	1.32	V
V_{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	–0.5	1.26	V
I_{DCIN}	DC input current for receiver input pins DC coupled $V_{MGTAVTT}$ = 1.2V	–	14	mA
I_{DCOUT}	DC output current for transmitter pins DC coupled $V_{MGTAVTT}$ = 1.2V	–	14	mA
XADC				
V_{CCADC}	XADC supply relative to GNDADC	–0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC	–0.5	2.0	V
Temperature				
T_{STG}	Storage temperature (ambient)	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies[6]	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies[6]	–	+260	°C
T_j	Maximum junction temperature[6]	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. The lower absolute voltage specification always applies.
3. For I/O operation, refer to the *7 Series FPGAs SelectIO Resources User Guide* (UG471).
4. The maximum limit applies to DC signals. For maximum undershoot and overshoot AC specifications, see Table 4 and Table 5.
5. See Table 10 for TMDS_33 specifications.
6. For soldering guidelines and thermal considerations, see the *7 Series FPGA Packaging and Pinout Specification* (UG475).

Table 2: **Recommended Operating Conditions[1][2]**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}[3]	Internal supply voltage	0.97	1.00	1.03	V
	Internal supply voltage for -1C devices with voltage identification (VID) bit programmed to run at 0.9V typical[4].	0.87	0.90	0.93	V
V_{CCBRAM}[3]	Block RAM supply voltage	0.97	1.00	1.03	V
	Block RAM supply voltage for -1C devices with voltage identification (VID) bit programmed to run at 0.9V typical[4].	0.87	0.90	1.03	V
V_{CCAUX}	Auxiliary supply voltage	1.71	1.80	1.89	V
V_{CCO}[5][6]	Supply voltage for 3.3V HR I/O banks	1.14	–	3.465	V
	Supply voltage for 1.8V HP I/O banks	1.14	–	1.89	V
V_{CCAUX_IO}	Auxiliary supply voltage when set to 1.8V	1.71	1.80	1.89	V
	Auxiliary supply voltage when set to 2.0V	1.94	2.00	2.06	V
V_{IN}[7]	I/O input voltage	–0.20	–	V_{CCO} + 0.2	V
	I/O input voltage (when V_{CCO} = 3.3V) for V_{REF} and differential I/O standards except TMDS_33[8]	–0.20	–	2.625	V
I_{IN}[9]	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{CCBATT}[10]	Battery voltage	1.0	–	1.89	V

Table 2: **Recommended Operating Conditions[1][2] *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
GTX and GTH Transceivers					
$V_{MGTAVCC}$[11]	Analog supply voltage for the GTX/GTH transceiver QPLL frequency range ≤ 10.3125 GHz[12][13]	0.97	1.0	1.08	V
	Analog supply voltage for the GTX/GTH transceiver QPLL frequency range > 10.3125 GHz	1.02	1.05	1.08	V
$V_{MGTAVTT}$[11]	Analog supply voltage for the GTX/GTH transmitter and receiver termination circuits	1.17	1.2	1.23	V
$V_{MGTVCCAUX}$[11]	Auxiliary analog Quad PLL (QPLL) voltage supply for the transceivers	1.75	1.80	1.85	V
$V_{MGTAVTTRCAL}$[11]	Analog supply voltage for the resistor calibration circuit of the GTX/GTH transceiver column	1.17	1.2	1.23	V
XADC					
V_{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V_{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	–	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	–	100	°C

Notes:

1. All voltages are relative to ground.
2. For the design of the power distribution system, consult the *7 Series FPGAs PCB Design and Pin Planning Guide* (UG483).
3. V_{CCINT} and V_{CCBRAM} should be connected to the same supply.
4. For more information on the VID bit see the *Lowering Power using the Voltage Identification Bit* application note (XAPP555).
5. Configuration data is retained even if V_{CCO} drops to 0V.
6. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
7. The lower absolute voltage specification always applies.
8. See Table 10 for TMDS_33 specifications.
9. A total of 200 mA per bank should not be exceeded.
10. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX}.
11. Each voltage listed requires the filter circuit described in the *7 Series FPGAs GTX/GTH Transceiver User Guide* (UG476).
12. For data rates ≤ 10.3125 Gb/s, $V_{MGTAVCC}$ should be 1.0V ±3% for lower power consumption.
13. For lower power consumption, $V_{MGTAVCC}$ should be 1.0V ±3% over the entire CPLL frequency range.

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[1]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	15	µA
C_{IN}[2]	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 3.3V	90	–	330	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	68	–	250	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	34	–	220	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	23	–	150	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	12	–	120	µA

Table 3: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ[1]	Max	Units
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 3.3V	68	–	330	µA
	Pad pull-down (when selected) @ V_{IN} = 1.8V	45	–	180	µA
I_{CCADC}	Analog supply current, analog circuits in powered up state	–	–	25	mA
I_{BATT}[3]	Battery supply current	–	–	150	nA
R_{IN_TERM}[4]	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_40) for commercial (C), industrial (I), and extended (E) temperature devices	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_50) for commercial (C), industrial (I), and extended (E) temperature devices	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to V_{CCO}/2 (UNTUNED_SPLIT_60) for commercial (C), industrial (I), and extended (E) temperature devices	44	60	83	Ω
n	Temperature diode ideality factor	–	1.010	–	–
r	Temperature diode series resistance	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a V_{CCO}/2 level.

Table 4: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for 3.3V HR I/O Banks[1]**

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.55	100	–0.40	100
		–0.45	61.7
		–0.50	25.8
		–0.55	11.0
V_{CCO} + 0.60	46.6	–0.60	4.77
V_{CCO} + 0.65	21.2	–0.65	2.10
V_{CCO} + 0.70	9.75	–0.70	0.94
V_{CCO} + 0.75	4.55	–0.75	0.43
V_{CCO} + 0.80	2.15	–0.80	0.20
V_{CCO} + 0.85	1.02	–0.85	0.09
V_{CCO} + 0.90	0.49	–0.90	0.04
V_{CCO} + 0.95	0.24	–0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 5: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for 1.8V HP I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI @–40°C to 100°C	AC Voltage Undershoot	% of UI @–40°C to 100°C
V_{CCO} + 0.55	100	–0.55	100
V_{CCO} + 0.60	50.0	–0.60	50.0
V_{CCO} + 0.65	50.0	–0.65	50.0
V_{CCO} + 0.70	47.0	–0.70	50.0
V_{CCO} + 0.75	21.2	–0.75	50.0
V_{CCO} + 0.80	9.71	–0.80	50.0
V_{CCO} + 0.85	4.51	–0.85	28.4
V_{CCO} + 0.90	2.12	–0.90	12.7
V_{CCO} + 0.95	1.01	–0.95	5.79

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Table 6: **Typical Quiescent Supply Current**

Symbol	Description	Device	Speed Grade			Units
			-3	-2/-2L/-2G	-1	
I_{CCINTQ}	Quiescent V_{CCINT} supply current	XC7V585T	1483	1483	1483	mA
		XC7V2000T	N/A	3756	3756	mA
		XC7VX330T	1012	1012	1012	mA
		XC7VX415T	1324	1324	1324	mA
		XC7VX485T	1578	1578	1578	mA
		XC7VX550T	2214	2214	2214	mA
		XC7VX690T	2214	2214	2214	mA
		XC7VX980T	N/A	2580	2580	mA
		XC7VX1140T	N/A	3448	3448	mA
I_{CCOQ}	Quiescent V_{CCO} supply current	XC7V585T	1	1	1	mA
		XC7V2000T	N/A	1	1	mA
		XC7VX330T	1	1	1	mA
		XC7VX415T	1	1	1	mA
		XC7VX485T	1	1	1	mA
		XC7VX550T	1	1	1	mA
		XC7VX690T	1	1	1	mA
		XC7VX980T	N/A	1	1	mA
		XC7VX1140T	N/A	1	1	mA

Table 6: **Typical Quiescent Supply Current *(Cont'd)***

Symbol	Description	Device	Speed Grade			Units
			-3	-2/-2L/-2G	-1	
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current	XC7V585T	114	114	114	mA
		XC7V2000T	N/A	315	315	mA
		XC7VX330T	73	73	73	mA
		XC7VX415T	88	88	88	mA
		XC7VX485T	104	104	104	mA
		XC7VX550T	147	147	147	mA
		XC7VX690T	147	147	147	mA
		XC7VX980T	N/A	183	183	mA
		XC7VX1140T	N/A	250	250	mA
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current	XC7V585T	2	2	2	mA
		XC7V2000T	N/A	2	2	mA
		XC7VX330T	2	2	2	mA
		XC7VX415T	2	2	2	mA
		XC7VX485T	2	2	2	mA
		XC7VX550T	2	2	2	mA
		XC7VX690T	2	2	2	mA
		XC7VX980T	N/A	2	2	mA
		XC7VX1140T	N/A	2	2	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current	XC7V585T	34	34	34	mA
		XC7V2000T	N/A	56	56	mA
		XC7VX330T	32	32	32	mA
		XC7VX415T	38	38	38	mA
		XC7VX485T	44	44	44	mA
		XC7VX550T	63	63	63	mA
		XC7VX690T	63	63	63	mA
		XC7VX980T	N/A	65	65	mA
		XC7VX1140T	N/A	81	81	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX}, V_{CCAUX_IO}, and V_{CCO} have the same recommended voltage levels then they can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTX/GTH transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} - V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} - V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 7 shows the minimum current, in addition to I_{CCQ}, that is required by Virtex-7 T and XT devices for proper power-on and configuration. If the current minimums shown in Table 6 and Table 7 are met, the device powers on after all five supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the XPower tools to estimate current drain on these supplies.

Table 7: **Power-On Current for Virtex-7 T and XT Devices**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	I_{CCAUX_IO}	I_{CCBRAM}	Units
	Typ(1)	Typ(1)	Typ(1)	Typ(1)	Typ(1)	
XC7V585T	I_{CCINTQ} + 2700	I_{CCAUXQ} + 40	I_{CCOQ} + 60 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 108	mA
XC7V2000T	I_{CCINTQ} + 4000	I_{CCAUXQ} + 80	I_{CCOQ} + 60 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 176	mA
XC7VX330T	I_{CCINTQ} + 1000	I_{CCAUXQ} + 65	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 95	mA
XC7VX415T	I_{CCINTQ} + 1200	I_{CCAUXQ} + 75	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 115	mA
XC7VX485T	I_{CCINTQ} + 1200	I_{CCAUXQ} + 80	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 40 mA per bank	$I_{CCBRAMQ}$ + 140	mA
XC7VX550T	I_{CCINTQ} + 3300	I_{CCAUXQ} + 143	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 57 mA per bank	$I_{CCBRAMQ}$ + 200	mA
XC7VX690T	I_{CCINTQ} + 3300	I_{CCAUXQ} + 143	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 57 mA per bank	$I_{CCBRAMQ}$ + 200	mA
XC7VX980T	I_{CCINTQ} + 6500	I_{CCAUXQ} + 202	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 60 mA per bank	$I_{CCBRAMQ}$ + 204	mA
XC7VX1140T	I_{CCINTQ} + 8000	I_{CCAUXQ} + 235	I_{CCOQ} + 40 mA per bank	$I_{CCOAUXIOQ}$ + 63 mA per bank	$I_{CCBRAMQ}$ + 256	mA

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate maximum power-on currents.

Table 8: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
T_{VCCAUX_IO}	Ramp time from GND to 90% of V_{CCAUX_IO}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	$T_J = 100°C$(1)	–	500	ms
		$T_J = 85°C$(1)	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 90% of $V_{MGTVCCAUX}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with a worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 9: **SelectIO DC Input and Output Levels(1)(2)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8	–8
HSTL_I_12	–0.300	V_{REF} – 0.080	V_{REF} + 0.080	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	6.3	–6.3
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8	–8
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16	–16
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16	–16
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 3	Note 3
LVCMOS15, LVDCI_15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 4	Note 4
LVCMOS18, LVDCI_18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS25	–0.300	0.700	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 6	Note 6
LVCMOS33	–0.300	0.800	2.000	3.450	0.400	V_{CCO} – 0.400	Note 6	Note 6
LVTTL	–0.300	0.800	2.000	3.450	0.400	2.400	Note 7	Note 7
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.1	–0.1
PCI33_3	–0.400	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.5	–0.5
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	14.25	–14.25
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.0	–13.0
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.9	–8.9
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.0	–13.0
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.9	–8.9
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8	–8
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.4	–13.4

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in 3.3V I/O banks.
3. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks and 4, 8, or 12 mA in HR I/O banks.
4. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, or 16 mA in HR I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, 12, or 16 mA in HP I/O banks and 4, 8, 12, 16, or 24 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, or 16 mA
7. Supported drive strengths of 4, 8, 12, 16, or 24 mA
8. For detailed interface specific DC voltage levels, see the *7 Series FPGAs SelectIO Resources User Guide* (UG471).

Table 10: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}[1]			V_{ID}[2]			V_{OCM}[3]			V_{OD}[4]		
	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max
BLVDS_25	0.300	1.200	1.425	0.100	–	–	–	1.250	–	Note 5		
MINI_LVDS_25	0.300	1.200	V_{CCAUX}	0.200	0.400	0.600	1.000	1.200	1.400	0.300	0.450	0.600
PPDS_25	0.200	0.900	V_{CCAUX}	0.100	0.250	0.400	0.500	0.950	1.400	0.100	0.250	0.400
RSDS_25	0.300	0.900	1.500	0.100	0.350	0.600	1.000	1.200	1.400	0.100	0.350	0.600
TMDS_33	2.700	2.965	3.230	0.150	0.675	1.200	V_{CCO}–0.405	V_{CCO}–0.300	V_{CCO}–0.190	0.400	0.600	0.800

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{OCM} is the output common mode voltage.
4. V_{OD} is the output differential voltage (Q – $\overline{Q}$).
5. V_{OD} for BLVDS will vary significantly depending on topology and loading.
6. LVDS_25 is specified in Table 12.
7. LVDS is specified in Table 13.

Table 11: **Complementary Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}[1]			V_{ID}[2]		V_{OL}[3]	V_{OH}[4]	I_{OL}	I_{OH}
	V, Min	V, Typ	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V_{CCO}–0.400	8.00	–8.00
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO}–0.400	8.00	–8.00
DIFF_HSTL_II	0.300	0.750	1.125	0.100	–	0.400	V_{CCO}–0.400	16.00	–16.00
DIFF_HSTL_II_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO}–0.400	16.00	–16.00
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.100	–0.100
DIFF_MOBILE_DDR	0.300	0.900	1.425	0.100	–	10% V_{CCO}	90% V_{CCO}	0.100	–0.100
DIFF_SSTL12	0.300	0.600	0.850	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	14.25	–14.25
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	13.0	–13.0
DIFF_SSTL135_R	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	8.9	–8.9
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	13.0	–13.0
DIFF_SSTL15_R	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	8.9	–8.9
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.470	(V_{CCO}/2) + 0.470	8.00	–8.00
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.600	(V_{CCO}/2) + 0.600	13.4	–13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – $\overline{Q}$).
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

LVDS DC Specifications (LVDS_25)

The LVDS standard is available in the HR I/O banks.

Table 12: **LVDS_25 DC Specifications(1)**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply voltage		2.375	2.500	2.625	V
V_{OH}	Output High voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.700	–	–	V
V_{ODIFF}	Differential output voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output common-mode voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential input voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input common-mode voltage		0.300	1.200	1.425	V

Notes:

1. Differential inputs for LVDS_25 can be placed in banks with V_{CCO} levels that are different from the required level for outputs. Consult the *7 Series FPGAs SelectIO Resources User Guide* (UG471) for more information.

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks.

Table 13: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply voltage		1.710	1.800	1.890	V
V_{OH}	Output High voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.825	–	–	V
V_{ODIFF}	Differential output voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output common-mode voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential input voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	Common-mode input voltage = 1.25V	100	350	600	mV
V_{ICM}	Input common-mode voltage	Differential input voltage = ±350 mV	0.300	1.200	1.425	V

Notes:

1. Differential inputs for LVDS can be placed in banks with V_{CCO} levels that are different from the required level for outputs. Consult the *7 Series FPGAs SelectIO Resources User Guide* (UG471) for more information.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in the ISE® Design Suite 14.5 and Vivado® Design Suite 2013.1 as outlined in Table 14.

Table 14: **Virtex-7 T and XT FPGA Speed Specification Version By Device/Speed Grade**

Version In:		Typical V_{CCINT}	Device
ISE 14.5	Vivado 2013.1	(Table 2)	
1.09	1.09	1.0V	XC7V585T, XC7VX485T
N/A	1.08	1.0V	XC7V2000T
1.08	1.08	1.0V	XC7VX330T, XC7VX415T, XC7VX550T, XC7VX690T, XC7VX980T
N/A	1.08	1.0V	XC7VX1140T

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Production Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Virtex-7 T and XT FPGAs.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 15 correlates the current status of each Virtex-7 T and XT device on a per speed grade basis.

Table 15: **Virtex-7 T and XT Device Speed Grade Designations**

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC7V585T			-3, -2, -2L, -1
XC7V2000T	-2L, -2G		-2, -1
XC7VX330T			-3, -2, -2L, -1
XC7VX415T			-3, -2, -2L, -1
XC7VX485T			-3, -2, -2L, -1
XC7VX550T			-3, -2, -2L, -1
XC7VX690T			-3, -2, -2L, -1
XC7VX980T	-2, -2L, -1		
XC7VX1140T	-2, -2L, -2G, -1		

Production Silicon and Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

Table 16 lists the production released Virtex-7 T and XT device, speed grade, and the minimum corresponding supported speed specification version and software revisions. The software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 16: **Virtex-7 T and XT Device Production Software and Speed Specification Release**

Device	Speed Grade Designations				
	-3	-2G	-2	-2L	-1
XC7V585T	Vivado 2012.4 v1.08 or ISE 14.2 v1.06	N/A	Vivado 2012.4 v1.08 or ISE 14.2 v1.06		
XC7V2000T	N/A		Vivado 2012.4 v1.07		Vivado 2012.4 v1.07
XC7VX330T	Vivado 2013.1 v1.08 or ISE 14.5 v1.08	N/A	Vivado 2013.1 v1.08 or ISE 14.5 v1.08		
XC7VX415T		N/A			
XC7VX485T	Vivado 2012.4 v1.08 or ISE 14.2 v1.06	N/A	Vivado 2012.4 v1.08 or ISE 14.2 v1.06		
XC7VX550T	Vivado 2013.1 v1.08 or ISE 14.5 v1.08	N/A	Vivado 2013.1 v1.08 or ISE 14.5 v1.08		
XC7VX690T	Vivado 2013.1 v1.08 or ISE 14.5 v1.08	N/A	Vivado 2013.1 v1.08 or ISE 14.5 v1.08		
XC7VX980T	N/A	N/A			
XC7VX1140T	N/A				

Notes:

1. Blank entries indicate a device and/or speed grade in advance or preliminary status.

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Virtex-7 T and XT devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the AC Switching Characteristics, page 12. In each table, the I/O bank type is either High Performance (HP) or High Range (HR).

Table 17: **Networking Applications Interface Performances**

Description	I/O Bank Type	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	HR	710	710	625	Mb/s
	HP	710	710	625	Mb/s
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 14)	HR	1250	1250	950	Mb/s
	HP	1600	1400	1250	Mb/s
SDR LVDS receiver (SFI-4.1)(1)	HR	710	710	625	Mb/s
	HP	710	710	625	Mb/s
DDR LVDS receiver (SPI-4.2)(1)	HR	1250	1250	950	Mb/s
	HP	1600	1400	1250	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 18: **Maximum Physical Interface (PHY) Rate for Memory Interfaces IP available with the Memory Interface Generator(1)(2)**

Memory Standard	I/O Bank Type	V_{CCAUX_IO}	Speed Grade			Units
			-3	-2/-2L/-2G	-1	
4:1 Memory Controllers						
DDR3	HP	2.0V	1866	1866	1600	Mb/s
	HP	1.8V	1600	1333	1066	Mb/s
	HR	N/A	1066	1066	800	Mb/s
DDR3L	HP	2.0V	1600	1600	1333	Mb/s
	HP	1.8V	1333	1066	800	Mb/s
	HR	N/A	800	800	667	Mb/s
DDR2	HP	2.0V	800	800	800	Mb/s
	HP	1.8V	800	800	800	Mb/s
	HR	N/A	800	800	800	Mb/s
RLDRAM III	HP	2.0V	800	667	667	MHz
	HP	1.8V	550	500	450	MHz
	HR	N/A	N/A			
2:1 Memory Controllers						
DDR3	HP	2.0V	1066	1066	800	Mb/s
	HP	1.8V	1066	1066	800	Mb/s
	HR	N/A	1066	1066	800	Mb/s
DDR3L	HP	2.0V	1066	1066	800	Mb/s
	HP	1.8V	1066	1066	800	Mb/s
	HR	N/A	800	800	667	Mb/s
DDR2	HP	2.0V	800	800	800	Mb/s
	HP	1.8V				
	HR	N/A				
QDR II+(3)	HP	2.0V	550	500	450	MHz
	HP	1.8V				
	HR	N/A	500	450	400	MHz
RLDRAM II	HP	2.0V	533	500	450	MHz
	HP	1.8V				
	HR	N/A				
LPDDR2	HP	2.0V	667	667	667	Mb/s
	HP	1.8V	667	667	667	Mb/s
	HR	N/A	667	667	667	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see the *7 Series FPGAs Memory Interface Solutions User Guide* (UG586).
2. When using the internal V_{REF}, the maximum data rate is 800 Mb/s (400 MHz).
3. The maximum QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations. Burst length 2 (BL = 2) implementations are limited to 333 MHz for all speed grades and I/O bank types.

IOB Pad Input/Output/3-State

Table 19 (3.3V high-range IOB (HR)) and Table 20 (1.8V high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than T_{IOTP} when the DCITERMDISABLE pin is used. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 19: **3.3V IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
LVTTL_S4	1.31	1.42	1.64	3.77	3.90	4.00	4.53	4.76	4.99	ns
LVTTL_S8	1.31	1.42	1.64	3.50	3.64	3.73	4.26	4.50	4.72	ns
LVTTL_S12	1.31	1.42	1.64	3.49	3.62	3.72	4.25	4.48	4.71	ns
LVTTL_S16	1.31	1.42	1.64	3.03	3.17	3.26	3.79	4.03	4.25	ns
LVTTL_S24	1.31	1.42	1.64	3.25	3.39	3.48	4.01	4.25	4.47	ns
LVTTL_F4	1.31	1.42	1.64	3.22	3.36	3.45	3.98	4.22	4.44	ns
LVTTL_F8	1.31	1.42	1.64	2.71	2.84	2.93	3.47	3.70	3.92	ns
LVTTL_F12	1.31	1.42	1.64	2.69	2.82	2.92	3.45	3.68	3.91	ns
LVTTL_F16	1.31	1.42	1.64	2.57	2.85	3.15	3.33	3.71	4.14	ns
LVTTL_F24	1.31	1.42	1.64	2.41	2.64	2.89	3.17	3.50	3.88	ns
LVDS_25(1)	0.64	0.68	0.80	1.36	1.47	1.55	2.12	2.33	2.54	ns
MINI_LVDS_25	0.68	0.70	0.79	1.36	1.47	1.55	2.12	2.33	2.54	ns
BLVDS_25(1)	0.65	0.69	0.80	1.83	2.02	2.20	2.59	2.88	3.19	ns
RSDS_25 (point to point)(1)	0.63	0.68	0.79	1.36	1.48	1.55	2.12	2.34	2.54	ns
PPDS_25(1)	0.65	0.69	0.80	1.36	1.49	1.58	2.12	2.35	2.57	ns
TMDS_33(1)	0.72	0.76	0.86	1.43	1.54	1.60	2.19	2.40	2.59	ns
PCI33_3(1)	1.28	1.41	1.65	2.71	3.08	3.52	3.47	3.94	4.51	ns
HSUL_12	0.63	0.64	0.71	1.77	1.90	2.00	2.53	2.76	2.99	ns
DIFF_HSUL_12	0.58	0.61	0.70	1.55	1.68	1.78	2.31	2.54	2.77	ns
HSTL_I_S	0.61	0.64	0.73	1.55	1.69	1.80	2.31	2.55	2.79	ns
HSTL_II_S	0.61	0.64	0.73	1.21	1.34	1.43	1.97	2.20	2.42	ns
HSTL_I_18_S	0.64	0.67	0.76	1.28	1.39	1.45	2.04	2.25	2.44	ns
HSTL_II_18_S	0.64	0.67	0.76	1.18	1.31	1.40	1.94	2.17	2.39	ns
DIFF_HSTL_I_S	0.63	0.67	0.77	1.42	1.54	1.61	2.18	2.40	2.60	ns
DIFF_HSTL_II_S	0.63	0.67	0.77	1.15	1.24	1.27	1.91	2.10	2.26	ns
DIFF_HSTL_I_18_S	0.65	0.69	0.78	1.27	1.38	1.43	2.03	2.24	2.42	ns
DIFF_HSTL_II_18_S	0.65	0.69	0.78	1.14	1.23	1.26	1.90	2.09	2.25	ns
HSTL_I_F	0.61	0.64	0.73	1.10	1.19	1.23	1.86	2.05	2.22	ns

Table 19: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
HSTL_II_F	0.61	0.64	0.73	1.05	1.18	1.28	1.81	2.04	2.27	ns
HSTL_I_18_F	0.64	0.67	0.76	1.05	1.18	1.28	1.81	2.04	2.27	ns
HSTL_II_18_F	0.64	0.67	0.76	1.03	1.14	1.23	1.79	2.00	2.22	ns
DIFF_HSTL_I_F	0.63	0.67	0.77	1.09	1.18	1.22	1.85	2.04	2.21	ns
DIFF_HSTL_II_F	0.63	0.67	0.77	1.02	1.11	1.14	1.78	1.97	2.13	ns
DIFF_HSTL_I_18_F	0.65	0.69	0.78	1.08	1.17	1.21	1.84	2.03	2.20	ns
DIFF_HSTL_II_18_F	0.65	0.69	0.78	1.01	1.10	1.13	1.77	1.96	2.12	ns
LVCMOS33_S4	1.31	1.40	1.60	3.77	3.90	4.00	4.53	4.76	4.99	ns
LVCMOS33_S8	1.31	1.40	1.60	3.49	3.62	3.72	4.25	4.48	4.71	ns
LVCMOS33_S12	1.31	1.40	1.60	3.05	3.18	3.28	3.81	4.04	4.27	ns
LVCMOS33_S16	1.31	1.40	1.60	3.06	3.43	3.88	3.82	4.29	4.87	ns
LVCMOS33_F4	1.31	1.40	1.60	3.22	3.36	3.45	3.98	4.22	4.44	ns
LVCMOS33_F8	1.31	1.40	1.60	2.71	2.84	2.93	3.47	3.70	3.92	ns
LVCMOS33_F12	1.31	1.40	1.60	2.57	2.85	3.15	3.33	3.71	4.14	ns
LVCMOS33_F16	1.31	1.40	1.60	2.44	2.69	2.96	3.20	3.55	3.95	ns
LVCMOS25_S4	1.08	1.16	1.32	3.08	3.22	3.31	3.84	4.08	4.30	ns
LVCMOS25_S8	1.08	1.16	1.32	2.85	2.98	3.07	3.61	3.84	4.06	ns
LVCMOS25_S12	1.08	1.16	1.32	2.44	2.57	2.67	3.20	3.43	3.66	ns
LVCMOS25_S16	1.08	1.16	1.32	2.79	2.92	3.01	3.55	3.78	4.00	ns
LVCMOS25_F4	1.08	1.16	1.32	2.71	2.84	2.93	3.47	3.70	3.92	ns
LVCMOS25_F8	1.08	1.16	1.32	2.14	2.28	2.37	2.90	3.14	3.36	ns
LVCMOS25_F12	1.08	1.16	1.32	2.15	2.29	2.52	2.91	3.15	3.51	ns
LVCMOS25_F16	1.08	1.16	1.32	1.92	2.17	2.45	2.68	3.03	3.44	ns
LVCMOS18_S4	0.64	0.66	0.74	1.55	1.68	1.78	2.31	2.54	2.77	ns
LVCMOS18_S8	0.64	0.66	0.74	2.14	2.28	2.37	2.90	3.14	3.36	ns
LVCMOS18_S12	0.64	0.66	0.74	2.14	2.28	2.37	2.90	3.14	3.36	ns
LVCMOS18_S16	0.64	0.66	0.74	1.49	1.62	1.72	2.25	2.48	2.71	ns
LVCMOS18_S24(1)	0.64	0.66	0.74	1.74	1.92	2.08	2.50	2.78	3.07	ns
LVCMOS18_F4	0.64	0.66	0.74	1.38	1.51	1.61	2.14	2.37	2.60	ns
LVCMOS18_F8	0.64	0.66	0.74	1.64	1.78	1.87	2.40	2.64	2.86	ns
LVCMOS18_F12	0.64	0.66	0.74	1.64	1.78	1.87	2.40	2.64	2.86	ns
LVCMOS18_F16	0.64	0.66	0.74	1.52	1.68	1.81	2.28	2.54	2.80	ns
LVCMOS18_F24(1)	0.64	0.66	0.74	1.34	1.46	1.55	2.10	2.32	2.54	ns
LVCMOS15_S4	0.66	0.69	0.81	1.86	2.00	2.09	2.62	2.86	3.08	ns
LVCMOS15_S8	0.66	0.69	0.81	2.05	2.18	2.28	2.81	3.04	3.27	ns
LVCMOS15_S12	0.66	0.69	0.81	1.83	2.03	2.23	2.59	2.89	3.22	ns
LVCMOS15_S16	0.66	0.69	0.81	1.76	1.95	2.13	2.52	2.81	3.12	ns

Table 19: **3.3V IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
LVCMOS15_F4	0.66	0.69	0.81	1.63	1.76	1.86	2.39	2.62	2.85	ns
LVCMOS15_F8	0.66	0.69	0.81	1.79	1.99	2.18	2.55	2.85	3.17	ns
LVCMOS15_F12	0.66	0.69	0.81	1.40	1.54	1.65	2.16	2.40	2.64	ns
LVCMOS15_F16	0.66	0.69	0.81	1.37	1.51	1.61	2.13	2.37	2.60	ns
LVCMOS12_S4	0.88	0.91	1.00	2.53	2.67	2.76	3.29	3.53	3.75	ns
LVCMOS12_S8	0.88	0.91	1.00	2.05	2.18	2.28	2.81	3.04	3.27	ns
LVCMOS12_S12(1)	0.88	0.91	1.00	1.75	1.89	1.98	2.51	2.75	2.97	ns
LVCMOS12_F4	0.88	0.91	1.00	1.94	2.07	2.17	2.70	2.93	3.16	ns
LVCMOS12_F8	0.88	0.91	1.00	1.50	1.64	1.73	2.26	2.50	2.72	ns
LVCMOS12_F12(1)	0.88	0.91	1.00	1.54	1.71	1.87	2.30	2.57	2.86	ns
SSTL135_S	0.61	0.64	0.73	1.27	1.40	1.50	2.03	2.26	2.49	ns
SSTL15_S	0.61	0.64	0.73	1.24	1.37	1.47	2.00	2.23	2.46	ns
SSTL18_I_S	0.64	0.67	0.76	1.59	1.74	1.85	2.35	2.60	2.84	ns
SSTL18_II_S	0.64	0.67	0.76	1.27	1.40	1.50	2.03	2.26	2.49	ns
DIFF_SSTL135_S	0.59	0.61	0.73	1.27	1.40	1.50	2.03	2.26	2.49	ns
DIFF_SSTL15_S	0.63	0.67	0.77	1.24	1.37	1.47	2.00	2.23	2.46	ns
DIFF_SSTL18_I_S	0.65	0.69	0.78	1.50	1.63	1.72	2.26	2.49	2.71	ns
DIFF_SSTL18_II_S	0.65	0.69	0.78	1.13	1.22	1.25	1.89	2.08	2.24	ns
SSTL135_F	0.61	0.64	0.73	1.04	1.17	1.26	1.80	2.03	2.25	ns
SSTL15_F	0.61	0.64	0.73	1.04	1.17	1.26	1.80	2.03	2.25	ns
SSTL18_I_F	0.64	0.67	0.76	1.12	1.22	1.26	1.88	2.08	2.25	ns
SSTL18_II_F	0.64	0.67	0.76	1.05	1.18	1.28	1.81	2.04	2.27	ns
DIFF_SSTL135_F	0.59	0.61	0.73	1.04	1.17	1.26	1.80	2.03	2.25	ns
DIFF_SSTL15_F	0.63	0.67	0.77	1.04	1.17	1.26	1.80	2.03	2.25	ns
DIFF_SSTL18_I_F	0.65	0.69	0.78	1.10	1.19	1.23	1.86	2.05	2.22	ns
DIFF_SSTL18_II_F	0.65	0.69	0.78	1.02	1.10	1.14	1.78	1.96	2.13	ns

Notes:

1. This I/O standard is only available in the 3.3V high-range (HR) banks.

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics**

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
LVDS	0.75	0.79	0.92	1.05	1.17	1.24	1.68	1.92	2.06	ns
HSUL_12	0.69	0.72	0.82	1.65	1.84	2.05	2.29	2.59	2.87	ns
DIFF_HSUL_12	0.69	0.72	0.82	1.65	1.84	2.05	2.29	2.59	2.87	ns
HSTL_I_S	0.68	0.72	0.82	1.15	1.28	1.38	1.79	2.03	2.20	ns
HSTL_II_S	0.68	0.72	0.82	1.05	1.17	1.26	1.69	1.93	2.08	ns
HSTL_I_18_S	0.70	0.72	0.82	1.12	1.24	1.34	1.75	2.00	2.16	ns
HSTL_II_18_S	0.70	0.72	0.82	1.06	1.18	1.26	1.70	1.94	2.08	ns
HSTL_I_12_S	0.68	0.72	0.82	1.14	1.27	1.37	1.78	2.02	2.20	ns
HSTL_I_DCI_S	0.68	0.72	0.82	1.11	1.23	1.33	1.74	1.99	2.15	ns
HSTL_II_DCI_S	0.68	0.72	0.82	1.05	1.17	1.26	1.69	1.93	2.08	ns
HSTL_II_T_DCI_S	0.70	0.72	0.82	1.15	1.28	1.38	1.78	2.03	2.20	ns
HSTL_I_DCI_18_S	0.70	0.72	0.82	1.11	1.23	1.33	1.74	1.99	2.15	ns
HSTL_II_DCI_18_S	0.70	0.72	0.82	1.05	1.16	1.24	1.69	1.92	2.06	ns
HSTL_II _T_DCI_18_S	0.70	0.72	0.82	1.11	1.23	1.33	1.74	1.99	2.15	ns
DIFF_HSTL_I_S	0.75	0.79	0.92	1.15	1.28	1.38	1.79	2.03	2.20	ns
DIFF_HSTL_II_S	0.75	0.79	0.92	1.05	1.17	1.26	1.69	1.93	2.08	ns
DIFF_HSTL_I_DCI_S	0.75	0.79	0.92	1.15	1.28	1.38	1.78	2.03	2.20	ns
DIFF_HSTL_II_DCI_S	0.75	0.79	0.92	1.05	1.17	1.26	1.69	1.93	2.08	ns
DIFF_HSTL_I_18_S	0.75	0.79	0.92	1.12	1.24	1.34	1.75	2.00	2.16	ns
DIFF_HSTL_II_18_S	0.75	0.79	0.92	1.06	1.18	1.26	1.70	1.94	2.08	ns
DIFF_HSTL_I_DCI_18_S	0.75	0.79	0.92	1.11	1.23	1.33	1.74	1.99	2.15	ns
DIFF_HSTL_II_DCI_18_S	0.75	0.79	0.92	1.05	1.16	1.24	1.69	1.92	2.06	ns
DIFF_HSTL_II _T_DCI_18_S	0.75	0.79	0.92	1.11	1.23	1.33	1.74	1.99	2.15	ns
HSTL_I_F	0.68	0.72	0.82	1.02	1.14	1.22	1.66	1.90	2.04	ns
HSTL_II_F	0.68	0.72	0.82	0.97	1.08	1.15	1.61	1.84	1.97	ns
HSTL_I_18_F	0.70	0.72	0.82	1.04	1.16	1.24	1.68	1.91	2.06	ns
HSTL_II_18_F	0.70	0.72	0.82	0.98	1.09	1.16	1.62	1.85	1.98	ns
HSTL_I_12_F	0.68	0.72	0.82	1.02	1.13	1.21	1.65	1.88	2.03	ns
HSTL_I_DCI_F	0.68	0.72	0.82	1.04	1.16	1.24	1.67	1.91	2.06	ns
HSTL_II_DCI_F	0.68	0.72	0.82	0.97	1.08	1.15	1.61	1.84	1.97	ns
HSTL_II_T_DCI_F	0.70	0.72	0.82	1.02	1.14	1.22	1.66	1.90	2.04	ns
HSTL_I_DCI_18_F	0.70	0.72	0.82	1.04	1.16	1.24	1.67	1.91	2.06	ns
HSTL_II_DCI_18_F	0.70	0.72	0.82	0.98	1.09	1.16	1.61	1.85	1.98	ns
HSTL_II _T_DCI_18_F	0.70	0.72	0.82	1.04	1.16	1.24	1.67	1.91	2.06	ns
DIFF_HSTL_I_F	0.75	0.79	0.92	1.02	1.14	1.22	1.66	1.90	2.04	ns
DIFF_HSTL_II_F	0.75	0.79	0.92	0.97	1.08	1.15	1.61	1.84	1.97	ns
DIFF_HSTL_I_DCI_F	0.75	0.79	0.92	1.02	1.14	1.22	1.66	1.90	2.04	ns
DIFF_HSTL_II_DCI_F	0.75	0.79	0.92	0.97	1.08	1.15	1.61	1.84	1.97	ns

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
DIFF_HSTL_I_18_F	0.75	0.79	0.92	1.04	1.16	1.24	1.68	1.91	2.06	ns
DIFF_HSTL_II_18_F	0.75	0.79	0.92	0.98	1.09	1.16	1.62	1.85	1.98	ns
DIFF_HSTL_I_DCI_18_F	0.75	0.79	0.92	1.04	1.16	1.24	1.67	1.91	2.06	ns
DIFF_HSTL_II_DCI_18_F	0.75	0.79	0.92	0.98	1.09	1.16	1.61	1.85	1.98	ns
DIFF_HSTL_II _T_DCI_18_F	0.75	0.79	0.92	1.04	1.16	1.24	1.67	1.91	2.06	ns
LVCMOS18_S2	0.47	0.50	0.60	3.95	4.28	4.85	4.59	5.04	5.67	ns
LVCMOS18_S4	0.47	0.50	0.60	2.67	2.98	3.43	3.31	3.73	4.26	ns
LVCMOS18_S6	0.47	0.50	0.60	2.14	2.38	2.72	2.77	3.14	3.54	ns
LVCMOS18_S8	0.47	0.50	0.60	1.98	2.21	2.52	2.61	2.97	3.35	ns
LVCMOS18_S12	0.47	0.50	0.60	1.70	1.91	2.17	2.34	2.67	2.99	ns
LVCMOS18_S16	0.47	0.50	0.60	1.57	1.75	1.97	2.20	2.51	2.79	ns
LVCMOS18_F2	0.47	0.50	0.60	3.50	3.87	4.48	4.14	4.63	5.30	ns
LVCMOS18_F4	0.47	0.50	0.60	2.23	2.50	2.87	2.87	3.25	3.69	ns
LVCMOS18_F6	0.47	0.50	0.60	1.80	2.00	2.26	2.43	2.76	3.08	ns
LVCMOS18_F8	0.47	0.50	0.60	1.46	1.72	2.04	2.10	2.47	2.86	ns
LVCMOS18_F12	0.47	0.50	0.60	1.26	1.40	1.53	1.89	2.16	2.35	ns
LVCMOS18_F16	0.47	0.50	0.60	1.19	1.33	1.44	1.83	2.08	2.26	ns
LVCMOS15_S2	0.59	0.62	0.73	3.55	3.89	4.45	4.19	4.65	5.27	ns
LVCMOS15_S4	0.59	0.62	0.73	2.45	2.70	3.06	3.08	3.45	3.89	ns
LVCMOS15_S6	0.59	0.62	0.73	2.24	2.51	2.88	2.88	3.26	3.71	ns
LVCMOS15_S8	0.59	0.62	0.73	1.91	2.16	2.49	2.55	2.91	3.31	ns
LVCMOS15_S12	0.59	0.62	0.73	1.77	1.98	2.23	2.41	2.73	3.05	ns
LVCMOS15_S16	0.59	0.62	0.73	1.62	1.81	2.02	2.26	2.56	2.84	ns
LVCMOS15_F2	0.59	0.62	0.73	3.38	3.69	4.18	4.02	4.44	5.00	ns
LVCMOS15_F4	0.59	0.62	0.73	2.04	2.21	2.44	2.68	2.97	3.26	ns
LVCMOS15_F6	0.59	0.62	0.73	1.47	1.74	2.09	2.10	2.50	2.91	ns
LVCMOS15_F8	0.59	0.62	0.73	1.31	1.46	1.61	1.95	2.22	2.43	ns
LVCMOS15_F12	0.59	0.62	0.73	1.21	1.34	1.45	1.84	2.10	2.27	ns
LVCMOS15_F16	0.59	0.62	0.73	1.18	1.31	1.41	1.82	2.07	2.23	ns
LVCMOS12_S2	0.64	0.67	0.78	3.38	3.80	4.48	4.02	4.55	5.30	ns
LVCMOS12_S4	0.64	0.67	0.78	2.62	2.94	3.43	3.26	3.70	4.25	ns
LVCMOS12_S6	0.64	0.67	0.78	2.05	2.33	2.72	2.69	3.08	3.54	ns
LVCMOS12_S8	0.64	0.67	0.78	1.94	2.18	2.51	2.58	2.94	3.33	ns
LVCMOS12_F2	0.64	0.67	0.78	2.84	3.15	3.62	3.48	3.90	4.44	ns
LVCMOS12_F4	0.64	0.67	0.78	1.97	2.18	2.44	2.61	2.93	3.26	ns
LVCMOS12_F6	0.64	0.67	0.78	1.33	1.51	1.70	1.96	2.26	2.52	ns
LVCMOS12_F8	0.64	0.67	0.78	1.27	1.42	1.55	1.91	2.18	2.37	ns
LVDCI_18	0.47	0.50	0.60	1.99	2.15	2.35	2.62	2.91	3.17	ns

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
LVDCI_15	0.59	0.62	0.73	1.98	2.23	2.58	2.62	2.99	3.40	ns
LVDCI_DV2_18	0.47	0.50	0.60	1.99	2.15	2.34	2.62	2.90	3.17	ns
LVDCI_DV2_15	0.59	0.62	0.73	1.98	2.23	2.58	2.62	2.99	3.40	ns
HSLVDCI_18	0.68	0.72	0.82	1.99	2.15	2.35	2.62	2.91	3.17	ns
HSLVDCI_15	0.68	0.72	0.82	1.98	2.23	2.58	2.62	2.99	3.40	ns
SSTL18_I_S	0.68	0.72	0.82	1.02	1.15	1.24	1.66	1.90	2.07	ns
SSTL18_II_S	0.68	0.72	0.82	1.17	1.29	1.37	1.81	2.05	2.19	ns
SSTL18_I_DCI_S	0.68	0.72	0.82	0.92	1.06	1.17	1.56	1.82	1.99	ns
SSTL18_II_DCI_S	0.68	0.72	0.82	0.88	0.98	1.08	1.51	1.74	1.90	ns
SSTL18_II_T_DCI_S	0.68	0.72	0.82	0.92	1.06	1.17	1.56	1.82	1.99	ns
SSTL15_S	0.68	0.72	0.82	0.94	1.06	1.15	1.58	1.82	1.97	ns
SSTL15_DCI_S	0.68	0.72	0.82	0.94	1.06	1.15	1.57	1.82	1.97	ns
SSTL15_T_DCI_S	0.68	0.72	0.82	0.94	1.06	1.15	1.57	1.82	1.97	ns
SSTL135_S	0.69	0.72	0.82	0.97	1.10	1.19	1.60	1.85	2.01	ns
SSTL135_DCI_S	0.69	0.72	0.82	0.97	1.09	1.19	1.60	1.85	2.01	ns
SSTL135_T_DCI_S	0.69	0.72	0.82	0.97	1.09	1.19	1.60	1.85	2.01	ns
SSTL12_S	0.69	0.72	0.82	0.96	1.09	1.18	1.60	1.84	2.00	ns
SSTL12_DCI_S	0.69	0.72	0.82	1.03	1.17	1.27	1.66	1.92	2.09	ns
SSTL12_T_DCI_S	0.69	0.72	0.82	1.03	1.17	1.27	1.66	1.92	2.09	ns
DIFF_SSTL18_I_S	0.75	0.79	0.92	1.02	1.15	1.24	1.66	1.90	2.07	ns
DIFF_SSTL18_II_S	0.75	0.79	0.92	1.17	1.29	1.37	1.81	2.05	2.19	ns
DIFF_SSTL18_I_DCI_S	0.75	0.79	0.92	0.92	1.06	1.17	1.56	1.82	1.99	ns
DIFF_SSTL18_II_DCI_S	0.75	0.79	0.92	0.88	0.98	1.08	1.51	1.74	1.90	ns
DIFF_SSTL18_II_T_DCI_S	0.75	0.79	0.92	0.92	1.06	1.17	1.56	1.82	1.99	ns
DIFF_SSTL15_S	0.68	0.72	0.82	0.94	1.06	1.15	1.58	1.82	1.97	ns
DIFF_SSTL15_DCI_S	0.68	0.72	0.82	0.94	1.06	1.15	1.57	1.82	1.97	ns
DIFF_SSTL15_T_DCI_S	0.68	0.72	0.82	0.94	1.06	1.15	1.57	1.82	1.97	ns
DIFF_SSTL135_S	0.69	0.72	0.82	0.97	1.10	1.19	1.60	1.85	2.01	ns
DIFF_SSTL135_DCI_S	0.69	0.72	0.82	0.97	1.09	1.19	1.60	1.85	2.01	ns
DIFF_SSTL135_T_DCI_S	0.69	0.72	0.82	0.97	1.09	1.19	1.60	1.85	2.01	ns
DIFF_SSTL12_S	0.69	0.72	0.82	0.96	1.09	1.18	1.60	1.84	2.00	ns
DIFF_SSTL12_DCI_S	0.69	0.72	0.82	1.03	1.17	1.27	1.66	1.92	2.09	ns
DIFF_SSTL12_T_DCI_S	0.69	0.72	0.82	1.03	1.17	1.27	1.66	1.92	2.09	ns
SSTL18_I_F	0.68	0.72	0.82	0.94	1.06	1.15	1.58	1.82	1.97	ns
SSTL18_II_F	0.68	0.72	0.82	0.97	1.09	1.16	1.61	1.84	1.99	ns
SSTL18_I_DCI_F	0.68	0.72	0.82	0.89	1.02	1.10	1.53	1.77	1.92	ns
SSTL18_II_DCI_F	0.68	0.72	0.82	0.89	1.02	1.10	1.53	1.77	1.92	ns
SSTL18_II_T_DCI_F	0.68	0.72	0.82	0.89	1.02	1.10	1.53	1.77	1.92	ns

Table 20: **1.8V IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	-3	-2/-2L/-2G	-1	
SSTL15_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
SSTL15_DCI_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
SSTL15_T_DCI_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
SSTL135_F	0.69	0.72	0.82	0.88	1.00	1.08	1.52	1.76	1.90	ns
SSTL135_DCI_F	0.69	0.72	0.82	0.89	1.00	1.08	1.52	1.76	1.90	ns
SSTL135_T_DCI_F	0.69	0.72	0.82	0.89	1.00	1.08	1.52	1.76	1.90	ns
SSTL12_F	0.69	0.72	0.82	0.88	1.00	1.08	1.52	1.76	1.90	ns
SSTL12_DCI_F	0.69	0.72	0.82	0.91	1.03	1.11	1.54	1.79	1.93	ns
SSTL12_T_DCI_F	0.69	0.72	0.82	0.91	1.03	1.11	1.54	1.79	1.93	ns
DIFF_SSTL18_I_F	0.75	0.79	0.92	0.94	1.06	1.15	1.58	1.82	1.97	ns
DIFF_SSTL18_II_F	0.75	0.79	0.92	0.97	1.09	1.16	1.61	1.84	1.99	ns
DIFF_SSTL18_I_DCI_F	0.75	0.79	0.92	0.89	1.02	1.10	1.53	1.77	1.92	ns
DIFF_SSTL18_II_DCI_F	0.75	0.79	0.92	0.89	1.02	1.10	1.53	1.77	1.92	ns
DIFF_SSTL18_II_T_DCI_F	0.75	0.79	0.92	0.89	1.02	1.10	1.53	1.77	1.92	ns
DIFF_SSTL15_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
DIFF_SSTL15_DCI_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
DIFF_SSTL15_T_DCI_F	0.68	0.72	0.82	0.89	1.01	1.09	1.53	1.77	1.91	ns
DIFF_SSTL135_F	0.69	0.72	0.82	0.88	1.00	1.08	1.52	1.76	1.90	ns
DIFF_SSTL135_DCI_F	0.69	0.72	0.82	0.89	1.00	1.08	1.52	1.76	1.90	ns
DIFF_SSTL135_T_DCI_F	0.69	0.72	0.82	0.89	1.00	1.08	1.52	1.76	1.90	ns
DIFF_SSTL12_F	0.69	0.72	0.82	0.88	1.00	1.08	1.52	1.76	1.90	ns
DIFF_SSTL12_DCI_F	0.69	0.72	0.82	0.91	1.03	1.11	1.54	1.79	1.93	ns
DIFF_SSTL12_T_DCI_F	0.69	0.72	0.82	0.91	1.03	1.11	1.54	1.79	1.93	ns

Notes:

1. This I/O standard is only available in the 1.8V high-performance (HP) banks.

Table 21 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than T_{IOTPHZ} when the DCITERMDISABLE pin is used. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 21: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
T_{IOTPHZ}	T input to pad high-impedance	0.76	0.86	0.99	ns
$T_{IOIBUFDISABLE\_HR}$	IBUF turn-on time from IBUFDISABLE to O output for HR I/O banks	1.72	1.89	2.14	ns
$T_{IOIBUFDISABLE\_HP}$	IBUF turn-on time from IBUFDISABLE to O output for HP I/O banks	1.31	1.46	1.76	ns

Input/Output Logic Switching Characteristics

Table 22: **ILOGIC Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
Setup/Hold					
T_{ICE1CK}/T_{ICKCE1}	CE1 pin setup/hold with respect to CLK	0.42/0.00	0.48/0.00	0.67/0.00	ns
T_{ISRCK}/T_{ICKSR}	SR pin setup/hold with respect to CLK	0.53/0.01	0.61/0.01	0.99/0.01	ns
$T_{IDOCKE2}/T_{IOCKDE2}$	D pin setup/hold with respect to CLK without delay (HP I/O banks only)	0.01/0.27	0.01/0.29	0.01/0.34	ns
$T_{IDOCKDE2}/T_{IOCKDDE2}$	DDLY pin setup/hold with respect to CLK (using IDELAY) (HP I/O banks only)	0.01/0.27	0.02/0.29	0.02/0.34	ns
$T_{IDOCKE3}/T_{IOCKDE3}$	D pin setup/hold with respect to CLK without delay (HR I/O banks only)	0.01/0.27	0.01/0.29	0.01/0.34	ns
$T_{IDOCKDE3}/T_{IOCKDDE3}$	DDLY pin setup/hold with respect to CLK (using IDELAY) (HR I/O banks only)	0.01/0.27	0.02/0.29	0.02/0.34	ns
Combinatorial					
T_{IDIE2}	D pin to O pin propagation delay, no delay (HP I/O banks only)	0.09	0.10	0.12	ns
T_{IDIDE2}	DDLY pin to O pin propagation delay (using IDELAY) (HP I/O banks only)	0.10	0.11	0.13	ns
T_{IDIE3}	D pin to O pin propagation delay, no delay (HR I/O banks only)	0.09	0.10	0.12	ns
T_{IDIDE3}	DDLY pin to O pin propagation delay (using IDELAY) (HR I/O banks only)	0.10	0.11	0.13	ns
Sequential Delays					
T_{IDLOE2}	D pin to Q1 pin using flip-flop as a latch without delay (HP I/O banks only)	0.36	0.39	0.45	ns
$T_{IDLODE2}$	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY) (HP I/O banks only)	0.36	0.39	0.45	ns
T_{IDLOE3}	D pin to Q1 pin using flip-flop as a latch without delay (HR I/O banks only)	0.36	0.39	0.45	ns
$T_{IDLODE3}$	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY) (HR I/O banks only)	0.36	0.39	0.45	ns
T_{ICKQ}	CLK to Q outputs	0.47	0.50	0.58	ns
$T_{RQ\_ILOGICE2}$	SR pin to OQ/TQ out (HP I/O banks only)	0.84	0.94	1.16	ns
$T_{GSRQ\_ILOGICE2}$	Global set/reset to Q outputs (HP I/O banks only)	7.60	7.60	10.51	ns
$T_{RQ\_ILOGICE3}$	SR pin to OQ/TQ out (HR I/O banks only)	0.84	0.94	1.16	ns
$T_{GSRQ\_ILOGICE3}$	Global set/reset to Q outputs (HR I/O banks only)	7.60	7.60	10.51	ns
Set/Reset					
$T_{RPW\_ILOGICE2}$	Minimum pulse width, SR inputs (HP I/O banks only)	0.54	0.63	0.63	ns, Min
$T_{RPW\_ILOGICE3}$	Minimum pulse width, SR inputs (HR I/O banks only)	0.54	0.63	0.63	ns, Min

Table 23: **OLOGIC Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
Setup/Hold					
T_{ODCK}/T_{OCKD}	D1/D2 pins setup/hold with respect to CLK	0.45/–0.13	0.50/–0.13	0.58/–0.13	ns
T_{OOCECK}/T_{OCKOCE}	OCE pin setup/hold with respect to CLK	0.28/0.03	0.29/0.03	0.45/0.03	ns
T_{OSRCK}/T_{OCKSR}	SR pin setup/hold with respect to CLK	0.32/0.18	0.38/0.18	0.70/0.18	ns
T_{OTCK}/T_{OCKT}	T1/T2 pins setup/hold with respect to CLK	0.49/–0.16	0.56/–0.16	0.68/–0.16	ns
T_{OTCECK}/T_{OCKTCE}	TCE pin setup/hold with respect to CLK	0.28/0.01	0.30/0.01	0.45/0.01	ns
Combinatorial					
T_{ODQ}	D1 to OQ out or T1 to TQ out	0.73	0.81	0.97	ns
Sequential Delays					
T_{OCKQ}	CLK to OQ/TQ out	0.41	0.43	0.49	ns
$T_{RQ\_OLOGICE2}$	SR pin to OQ/TQ out (HP I/O banks only)	0.63	0.70	0.83	ns
$T_{GSRQ\_OLOGICE2}$	Global set/reset to Q outputs (HP I/O banks only)	7.60	7.60	10.51	ns
$T_{RQ\_OLOGICE3}$	SR pin to OQ/TQ out (HR I/O banks only)	0.63	0.70	0.83	ns
$T_{GSRQ\_OLOGICE3}$	Global set/reset to Q outputs (HR I/O banks only)	7.60	7.60	10.51	ns
Set/Reset					
$T_{RPW\_OLOGICE2}$	Minimum pulse width, SR inputs (HP I/O banks only)	0.54	0.54	0.63	ns, Min
$T_{RPW\_OLOGICE3}$	Minimum pulse width, SR inputs (HR I/O banks only)	0.54	0.54	0.63	ns, Min

Input Serializer/Deserializer Switching Characteristics

Table 24: **ISERDES Switching Characteristics**

Symbol	Description	Speed Grade			Units
		-3	-2/-2L/-2G	-1	
Setup/Hold for Control Lines					
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin setup/hold with respect to CLKDIV	0.01/0.12	0.02/0.13	0.02/0.15	ns
T_{ISCCK_CE} / T_{ISCKC_CE}(2)	CE pin setup/hold with respect to CLK (for CE1)	0.39/–0.02	0.44/–0.02	0.63/–0.02	ns
T_{ISCCK_CE2} / T_{ISCKC_CE2}(2)	CE pin setup/hold with respect to CLKDIV (for CE2)	–0.12/0.29	–0.12/0.31	–0.12/0.35	ns
Setup/Hold for Data Lines					
T_{ISDCK_D} /T_{ISCKD_D}	D pin setup/hold with respect to CLK	–0.02/0.11	–0.02/0.12	–0.02/0.15	ns
T_{ISDCK_DDLY} /T_{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY)(1)	–0.02/0.11	–0.02/0.12	–0.02/0.15	ns
$T_{ISDCK\_D\_DDR}$ / $T_{ISCKD\_D\_DDR}$	D pin setup/hold with respect to CLK at DDR mode	–0.02/0.11	–0.02/0.12	–0.02/0.15	ns
$T_{ISDCK\_DDLY\_DDR}$/ $T_{ISCKD\_DDLY\_DDR}$	D pin setup/hold with respect to CLK at DDR mode (using IDELAY)(1)	0.11/0.11	0.12/0.12	0.15/0.15	ns
Sequential Delays					
T_{ISCKO_Q}	CLKDIV to out at Q pin	0.46	0.47	0.58	ns
Propagation Delays					
T_{ISDO_DO}	D input to DO output pin	0.09	0.10	0.12	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCCK_CE2} and T_{ISCKC_CE2} are reported as T_{ISCCK_CE}/T_{ISCKC_CE} in the timing report.